

Abstract Submitted  
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**Focused ion beam lithographically patterned growth of vertically aligned ZnO nanorods arrays on GaN** WING LUN CHUNG, HUA SHENG WU, Physics Department, The University of Hong Kong — Ordered ZnO nanorods were synthesized on GaN by using hydrothermal method via silicon dioxide template etched by focused ion beam nanolithography. Due to the nucleation site confinement, the as-grown ZnO nanorods were selectively budding inside the nanopattern. Scanning electron microscope image showed that the as-grown ZnO nanorods were highly ordered and exhibited hexagonal structure. This indicated the GaN substrate retained its crystalline orientation despite the destructive Focused ion beam lithography.

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